

directing a pulsed laser beam having a cross section elongated in one direction to said glass substrate;

B1
cancel
moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed laser beam, thereby irradiating said semiconductor islands with said pulsed laser beam.

2. (Amended) A method according to claim 1 wherein an energy density of said pulsed laser beam is not higher than 300 mJ/cm^2 .

4. (Amended) A method according to claim 1 wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed laser beam.

5. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

B2
forming a semiconductor film over a glass substrate;
crystallizing said semiconductor film;
patterning the crystallized semiconductor film into a plurality of semiconductor islands;
subjecting said semiconductor islands to an ion doping;
directing a pulsed laser beam having a cross section elongated in one direction to said glass substrate;
moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed laser beam, thereby irradiating said semiconductor islands with said pulsed laser beam.

6. (Amended) A method according to claim 5 wherein an energy density of said pulsed laser beam is not higher than 300 mJ/cm^2 .

B3
8. (Amended) A method according to claim 5 wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed laser beam.

9. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of first semiconductor islands and a plurality of second semiconductor islands over a glass substrate;

subjecting both of said first and second semiconductor islands to a first ion doping for introducing a first impurity;

subjecting only said first semiconductor islands to a second ion doping for introducing a second impurity wherein said second impurity has an opposite conductivity type to said first impurity;

directing a pulsed laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed laser beam, thereby irradiating both of said first and second semiconductor islands with said pulsed laser beam.

10. (Amended) A method according to claim 9 wherein an energy density of said pulsed laser beam is not higher than 300 mJ/cm^2 .

12. (Amended) A method according to claim 9 wherein each of said first and second semiconductor islands is irradiated with plural pulses of said pulsed laser beam.

13. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of semiconductor islands over a glass substrate;

forming a film comprising silicon oxide over said glass substrate wherein said semiconductor islands are covered by said film;

subjecting said semiconductor islands to an ion doping through said film;

directing a pulsed laser beam having a cross section elongated in one direction to said glass substrate;

b4
cancel

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed laser beam, thereby irradiating said semiconductor islands with said pulsed laser beam through said film.

14. (Amended) A method according to claim 13 wherein an energy density of said pulsed laser beam is not higher than 300 mJ/cm^2 .

16. (Amended) A method according to claim 13 wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed laser beam.


b6

17. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

- preparing a plurality of semiconductor islands comprising silicon and germanium over a substrate;
- subjecting said semiconductor islands to an ion doping;
- directing a pulsed laser beam having a cross section elongated in one direction to said glass substrate;
- moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed laser beam, thereby irradiating said semiconductor islands with said pulsed laser beam.

19. (Amended) A method of manufacturing a semiconductor device comprising the steps of:


- preparing a plurality of semiconductor islands comprising silicon and germanium over a substrate;
- forming a film comprising silicon oxide over said glass substrate wherein said semiconductor islands are covered by said film;
- subjecting said semiconductor islands to an ion doping through said film;
- directing a pulsed laser beam having a cross section elongated in one direction to said glass substrate;

 moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed laser beam, thereby irradiating said semiconductor islands with said pulsed laser beam through said film.

← Please add new claims 21-26 as follows:

--21. (New) The method of claim 1, wherein said pulsed laser beam is a pulsed excimer laser beam.

22. (New) The method of claim 5, wherein said pulsed laser beam is a pulsed excimer laser beam.

 23. (New) The method of claim 9, wherein said pulsed laser beam is a pulsed excimer laser beam.

24. (New) The method of claim 13, wherein said pulsed laser beam is a pulsed excimer laser beam.

25. (New) The method of claim 17, wherein said pulsed laser beam is a pulsed excimer laser beam.

26. (New) The method of claim 19, wherein said pulsed laser beam is a pulsed excimer laser beam.--

REMARKS

The Office Action of October 9, 2002 was received and carefully reviewed. Reconsideration and withdrawal of the currently pending rejections are requested for the reasons advanced in detail below.

Filed concurrently herewith is a *Request for a Two Month Extension of Time* which extends the shortened statutory period of response to March 9, 2002. Accordingly, Applicants respectfully submit that this response is being timely filed.